



# Thyristor Module

$V_{RRM} = 2 \times 1200 \text{ V}$

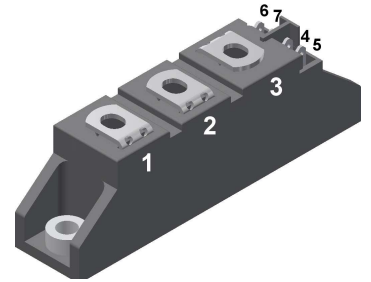
$I_{TAV} = 85 \text{ A}$

$V_T = 1.18 \text{ V}$

Phase leg

Part number

**MCMA85P1200TA**



Backside: isolated



### Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al<sub>2</sub>O<sub>3</sub>-ceramic

### Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

### Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

### Disclaimer Notice

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| Thyristor      |  |   |                           | Ratings |      |                   |  |
|----------------|--|---|---------------------------|---------|------|-------------------|--|
| Symbol         | Definition   | Conditions  | min.                      | typ.    | max. | Unit              |  |
| $V_{RSM/DSM}$  | max. non-repetitive reverse/forward blocking voltage | $T_{VJ} = 25^{\circ}C$  |                           |         | 1300 | V                 |  |
| $V_{RRM/DRM}$  | max. repetitive reverse/forward blocking voltage     | $T_{VJ} = 25^{\circ}C$  |                           |         | 1200 | V                 |  |
| $I_{RD}$       | reverse current, drain current                       | $V_{R/D} = 1200 V$  | $T_{VJ} = 25^{\circ}C$    |         | 100  | $\mu A$           |  |
|                |  | $V_{R/D} = 1200 V$  | $T_{VJ} = 140^{\circ}C$   |         | 10   | mA                |  |
| $V_T$          | forward voltage drop                                 | $I_T = 85 A$  | $T_{VJ} = 25^{\circ}C$    |         | 1.21 | V                 |  |
|                |  | $I_T = 170 A$   |                           |         | 1.47 | V                 |  |
|                |  | $I_T = 85 A$  | $T_{VJ} = 125^{\circ}C$   |         | 1.18 | V                 |  |
|                |  | $I_T = 170 A$   |                           |         | 1.51 | V                 |  |
| $I_{TAV}$      | average forward current                              | $T_C = 85^{\circ}C$   | $T_{VJ} = 140^{\circ}C$   |         | 85   | A                 |  |
| $I_{T(RMS)}$   | RMS forward current                                  | 180° sine   |                           |         | 135  | A                 |  |
| $V_{T0}$       | threshold voltage                                    | } for power loss calculation only   | $T_{VJ} = 140^{\circ}C$   |         | 0.85 | V                 |  |
| $r_T$          | slope resistance                                     |   |                           |         | 3.9  | m $\Omega$        |  |
| $R_{thJC}$     | thermal resistance junction to case                  |   |                           |         | 0.38 | K/W               |  |
| $R_{thCH}$     | thermal resistance case to heatsink                  |   |                           | 0.2     |      | K/W               |  |
| $P_{tot}$      | total power dissipation                              |   | $T_C = 25^{\circ}C$       |         | 300  | W                 |  |
| $I_{TSM}$      | max. forward surge current                           | $t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$  | $T_{VJ} = 45^{\circ}C$    |         | 1.50 | kA                |  |
|                |  | $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$   | $V_R = 0 V$               |         | 1.62 | kA                |  |
|                |  | $t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$  | $T_{VJ} = 140^{\circ}C$   |         | 1.28 | kA                |  |
|                |  | $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$   | $V_R = 0 V$               |         | 1.38 | kA                |  |
| $I^2t$         | value for fusing                                     | $t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$  | $T_{VJ} = 45^{\circ}C$    |         | 11.3 | kA <sup>2</sup> s |  |
|                |  | $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$   | $V_R = 0 V$               |         | 10.9 | kA <sup>2</sup> s |  |
|                |  | $t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$  | $T_{VJ} = 140^{\circ}C$   |         | 8.13 | kA <sup>2</sup> s |  |
|                |  | $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$   | $V_R = 0 V$               |         | 7.87 | kA <sup>2</sup> s |  |
| $C_J$          | junction capacitance                                 | $V_R = 400 V \quad f = 1 \text{ MHz}$   | $T_{VJ} = 25^{\circ}C$    |         | 74   | pF                |  |
| $P_{GM}$       | max. gate power dissipation                          | $t_p = 30 \mu s$  | $T_C = 140^{\circ}C$      |         | 10   | W                 |  |
|                |  | $t_p = 300 \mu s$   |                           |         | 5    | W                 |  |
| $P_{GAV}$      | average gate power dissipation                       |   |                           |         | 0.5  | W                 |  |
| $(di/dt)_{cr}$ | critical rate of rise of current                     | $T_{VJ} = 140^{\circ}C; f = 50 \text{ Hz}$  | repetitive, $I_T = 255 A$ |         | 150  | A/ $\mu s$        |  |
|                |  | $t_p = 200 \mu s; di_G/dt = 0.45 A/\mu s;$<br>$I_G = 0.45 A; V = \frac{2}{3} V_{DRM}$                                     | non-repet., $I_T = 85 A$  |         | 500  | A/ $\mu s$        |  |
| $(dv/dt)_{cr}$ | critical rate of rise of voltage                     | $V = \frac{2}{3} V_{DRM}$<br>$R_{GK} = \infty; \text{ method 1 (linear voltage rise)}$                                    | $T_{VJ} = 140^{\circ}C$   |         | 1000 | V/ $\mu s$        |  |
| $V_{GT}$       | gate trigger voltage                                 | $V_D = 6 V$   | $T_{VJ} = 25^{\circ}C$    |         | 1.5  | V                 |  |
|                |  |   | $T_{VJ} = -40^{\circ}C$   |         | 1.6  | V                 |  |
| $I_{GT}$       | gate trigger current                                 | $V_D = 6 V$   | $T_{VJ} = 25^{\circ}C$    |         | 95   | mA                |  |
|                |  |   | $T_{VJ} = -40^{\circ}C$   |         | 200  | mA                |  |
| $V_{GD}$       | gate non-trigger voltage                             | $V_D = \frac{2}{3} V_{DRM}$   | $T_{VJ} = 140^{\circ}C$   |         | 0.2  | V                 |  |
| $I_{GD}$       | gate non-trigger current                             |   |                           |         | 10   | mA                |  |
| $I_L$          | latching current                                     | $t_p = 10 \mu s$  | $T_{VJ} = 25^{\circ}C$    |         | 200  | mA                |  |
|                |  | $I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$  |                           |         |      |                   |  |
| $I_H$          | holding current                                      | $V_D = 6 V \quad R_{GK} = \infty$   | $T_{VJ} = 25^{\circ}C$    |         | 200  | mA                |  |
| $t_{gd}$       | gate controlled delay time                           | $V_D = \frac{1}{2} V_{DRM}$   | $T_{VJ} = 25^{\circ}C$    |         | 2    | $\mu s$           |  |
|                |  | $I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$  |                           |         |      |                   |  |
| $t_q$          | turn-off time  | $V_R = 100 V; I_T = 85 A; V = \frac{2}{3} V_{DRM}$<br>$di/dt = 10 A/\mu s \quad dv/dt = 20 V/\mu s \quad t_p = 200 \mu s$ | $T_{VJ} = 125^{\circ}C$   |         | 150  | $\mu s$           |  |



| Package TO-240AA |  |                      |                                     | Ratings |      |      |  |
|------------------|--|----------------------|-------------------------------------|---------|------|------|--|
| Symbol           | Definition   | Conditions           | min.                                | typ.    | max. | Unit |  |
| $I_{RMS}$        | RMS current  | per terminal         |                                     |         | 150  | A    |  |
| $T_{VJ}$         | virtual junction temperature                                 |                      | -40                                 |         | 140  | °C   |  |
| $T_{op}$         | operation temperature  |                      | -40                                 |         | 125  | °C   |  |
| $T_{stg}$        | storage temperature  |                      | -40                                 |         | 125  | °C   |  |
| <b>Weight</b>    |  |                      |                                     |         | 81   | g    |  |
| $M_D$            | mounting torque  |                      | 2.5                                 |         | 4    | Nm   |  |
| $M_T$            | terminal torque  |                      | 2.5                                 |         | 4    | Nm   |  |
| $d_{Spp/App}$    | creepage distance on surface   striking distance through air | terminal to terminal | 13.0                                | 9.7     |      | mm   |  |
| $d_{Spb/Apb}$    |  | terminal to backside | 16.0                                | 16.0    |      | mm   |  |
| $V_{ISOL}$       | isolation voltage  | t = 1 second         |                                     | 4800    |      | V    |  |
|                  |  | t = 1 minute         | 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA | 4000    |      | V    |  |



**Part description**

- M = Module
- C = Thyristor (SCR)
- M = Thyristor
- A = (up to 1800V)
- 85 = Current Rating [A]
- P = Phase leg
- 1200 = Reverse Voltage [V]
- TA = TO-240AA-1B

| Ordering | Ordering Number | Marking on Product | Delivery Mode | Quantity | Code No. |
|----------|-----------------|--------------------|---------------|----------|----------|
| Standard | MCMA85P1200TA   | MCMA85P1200TA      | Box           | 36       | 512923   |

**Equivalent Circuits for Simulation**

\* on die level

$T_{VJ} = 140^{\circ}C$



**Thyristor**

|              |                    |      |    |
|--------------|--------------------|------|----|
| $V_{0\ max}$ | threshold voltage  | 0.85 | V  |
| $R_{0\ max}$ | slope resistance * | 2.7  | mΩ |



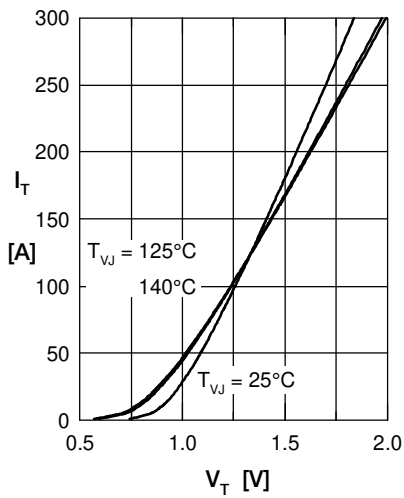
**Thyristor**


Fig. 1 Forward characteristics

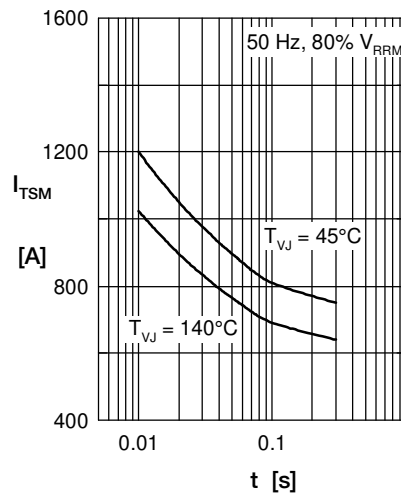
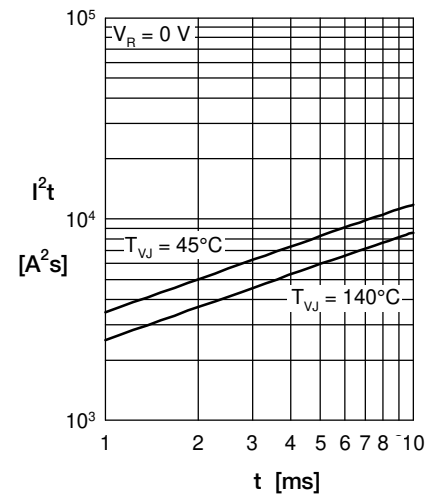
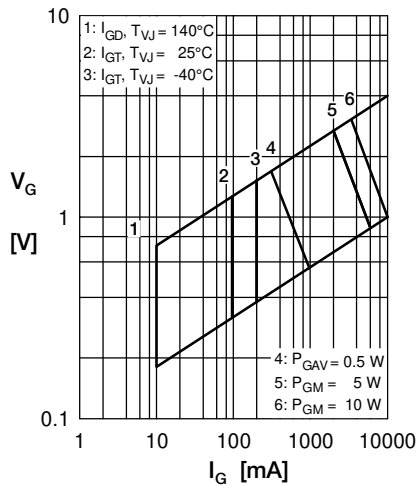

 Fig. 2 Surge overload current  
 $I_{TSM}$ : crest value,  $t$ : duration

 Fig. 3  $I^2t$  versus time (1-10 s)


Fig. 4 Gate voltage &amp; gate current

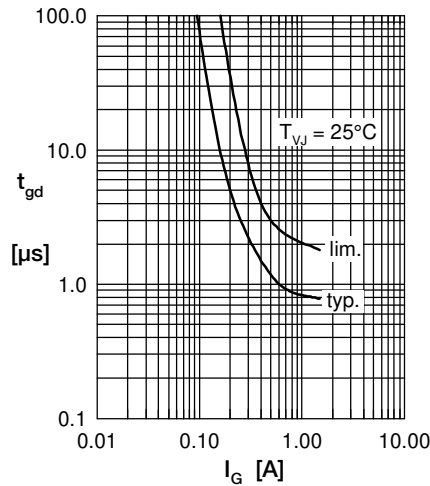
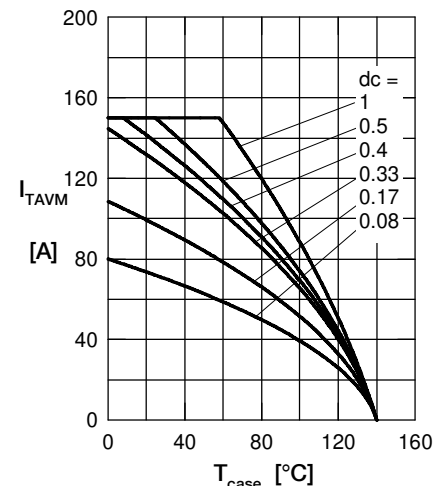

 Fig. 5 Gate controlled delay time  $t_{gd}$ 


Fig. 6 Max. forward current at case temperature

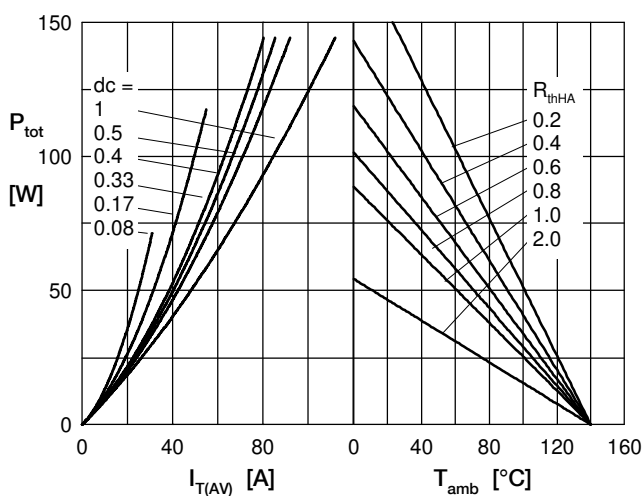
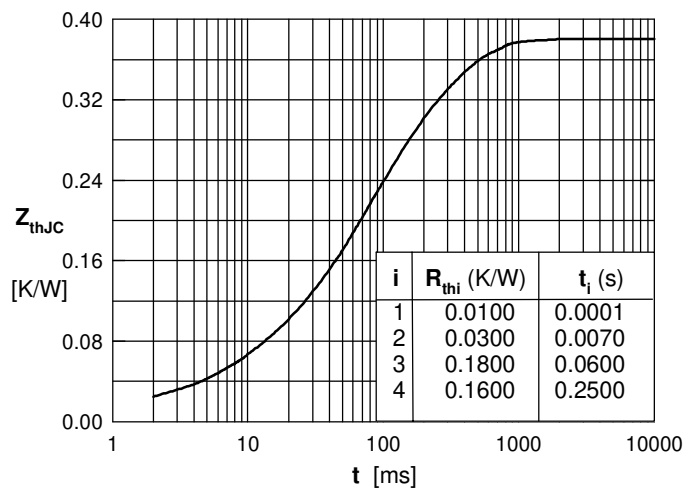

 Fig. 7a Power dissipation versus direct output current  
 Fig. 7b and ambient temperature


Fig. 8 Transient thermal impedance junction to case